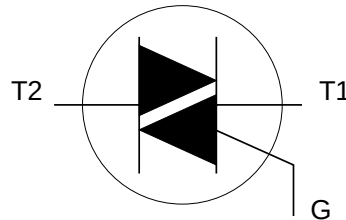


GENERAL DESCRIPTION

Glass passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

SYMBOL

TO-220AB

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	BT138-500	600	800	V
		500F	600F	800F	
		500G	600G	800G	
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	95	A

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99^\circ C$	-	12			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ C$ prior to surge $t = 20$ ms	-	95			A
		$t = 16.7$ ms	-	105			A
I^2t	I^2t for fusing	$t = 10$ ms	-	45			A ² s
di_t/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20$ A; $I_G = 0.2$ A; $di_G/dt = 0.2$ A/ μ s	-	50			A/ μ s
		T2+ G+	-	50			A/ μ s
		T2+ G-	-	50			A/ μ s
		T2- G-	-	50			A/ μ s
		T2- G+	-	10			A/ μ s
I_{GM}	Peak gate current		-	2			A
V_{GM}	Peak gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			$^\circ C$
T_j	Operating junction temperature		-	125			$^\circ C$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

THERMAL RESISTANCES

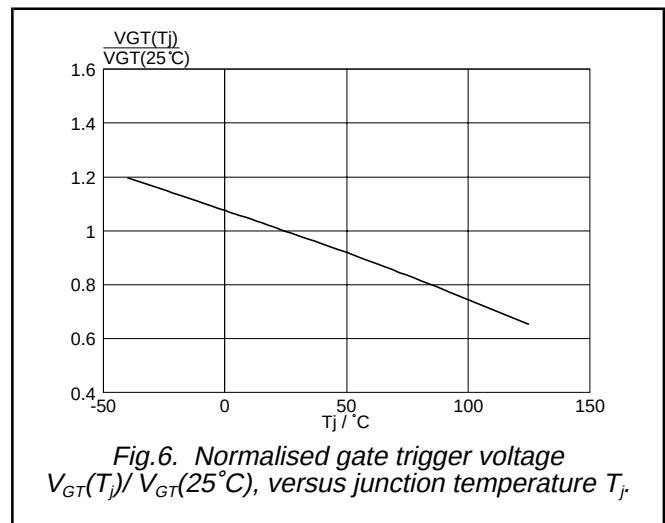
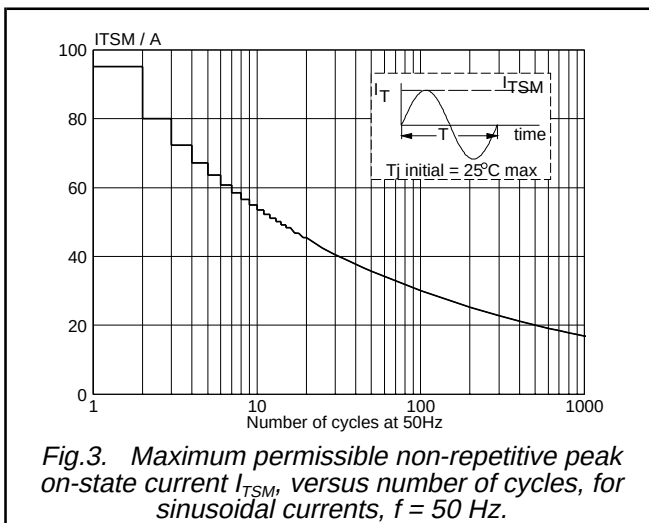
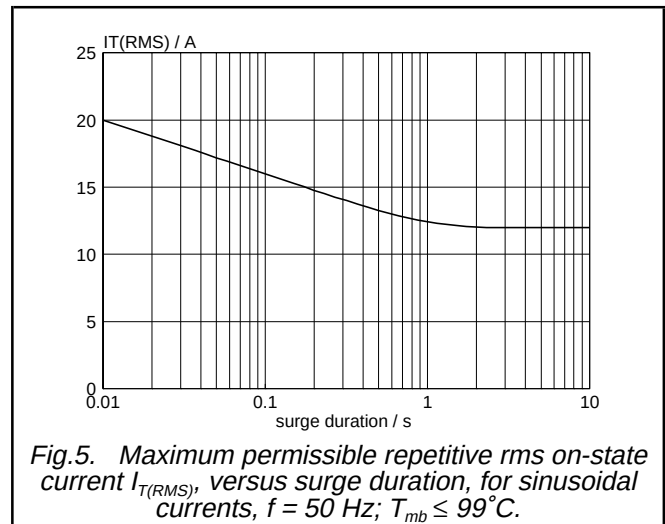
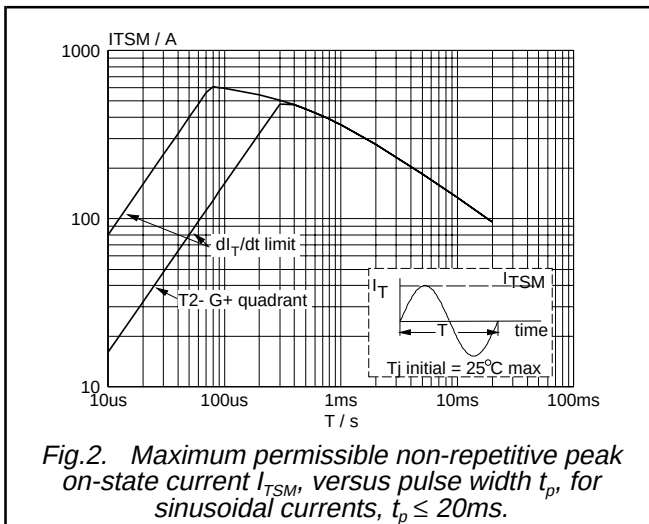
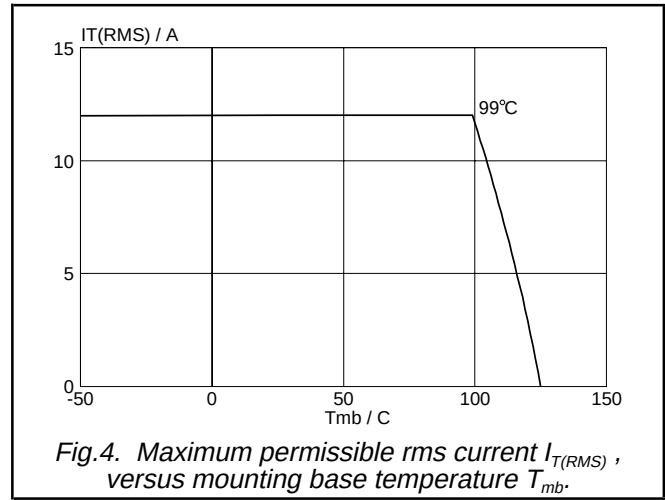
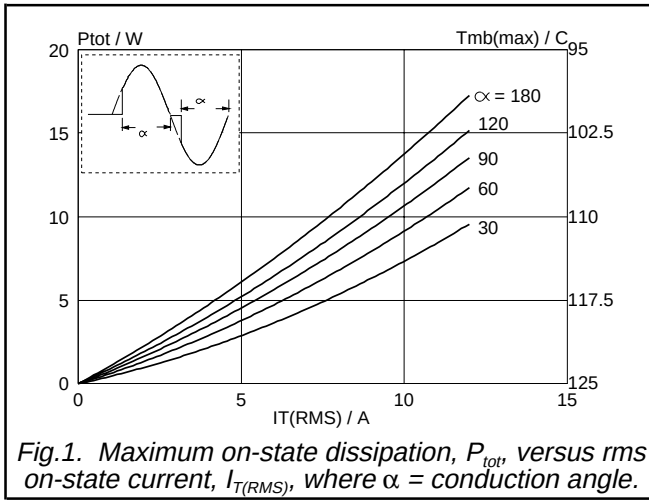
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle	-	-	2.0	K/W
		in free air	-	60	-	K/W

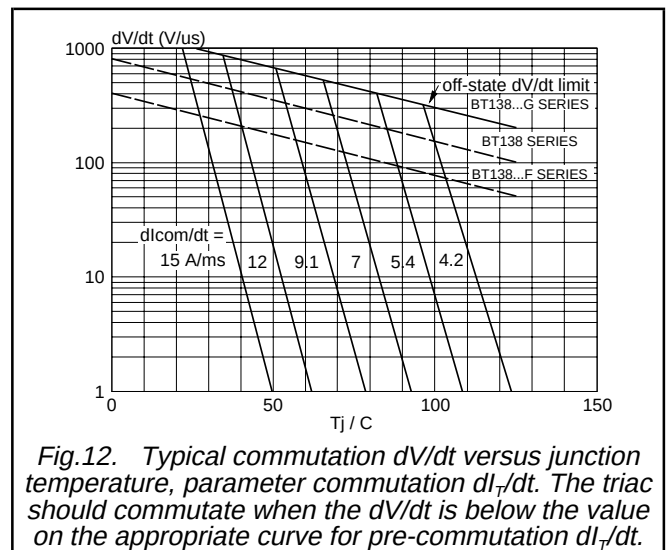
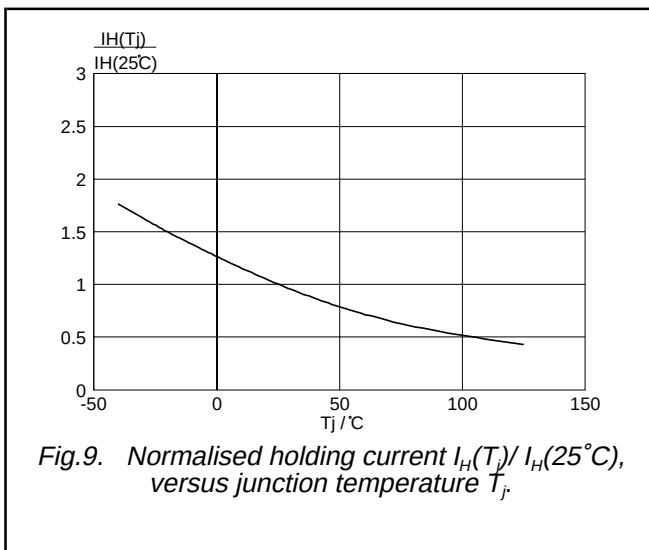
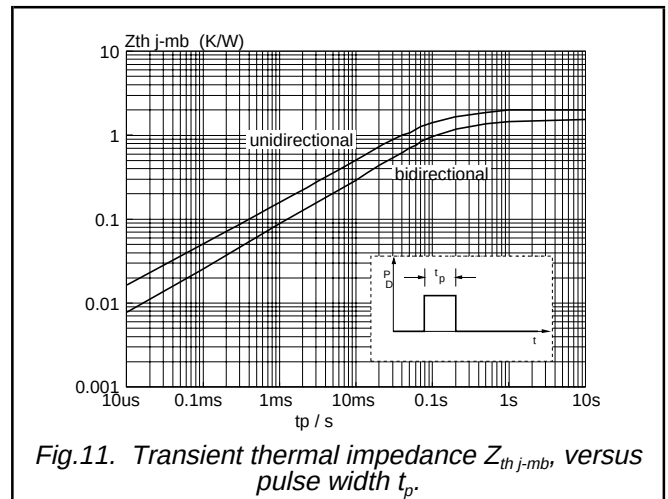
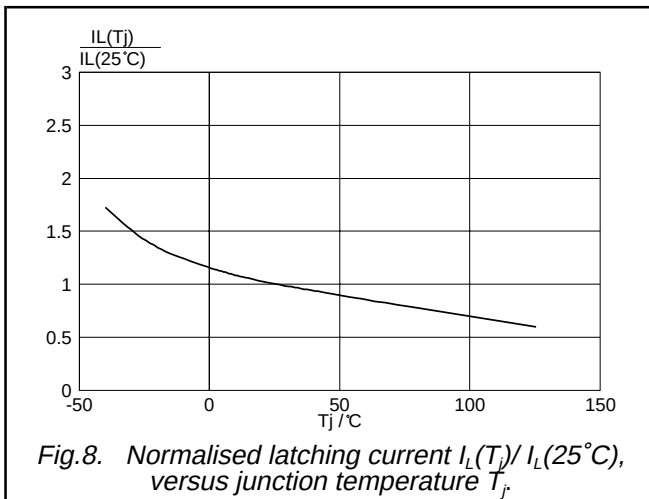
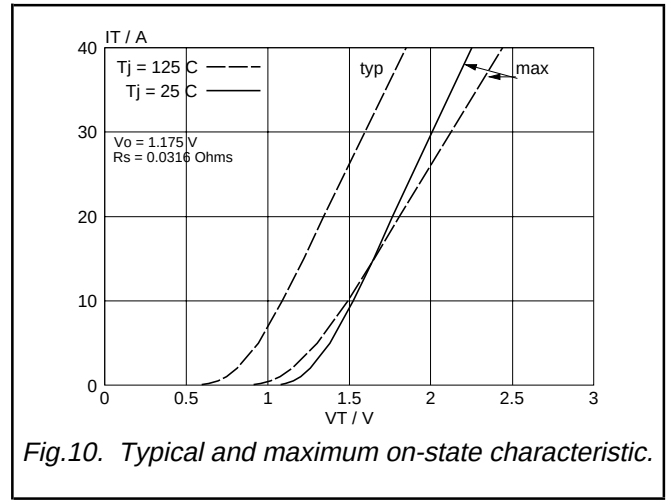
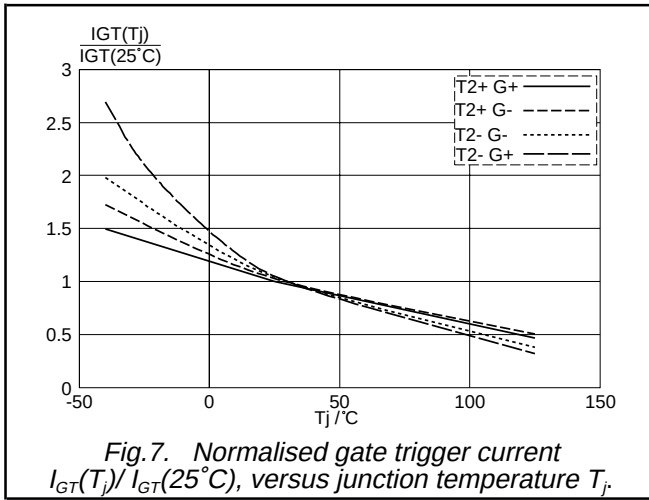
STATIC CHARACTERISTICS
 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
I_{GT}	Gate trigger current	BT138- $V_D = 12\text{ V}; I_T = 0.1\text{ A}$			...	...F	...G	
		T2+ G+	-	5	35	25	50	mA
		T2+ G-	-	8	35	25	50	mA
		T2- G-	-	10	35	25	50	mA
		T2- G+	-	22	70	70	100	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$						
		T2+ G+	-	7	40	40	60	mA
		T2+ G-	-	20	60	60	90	mA
		T2- G-	-	8	40	40	60	mA
		T2- G+	-	10	60	60	90	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	6	30	30	60	mA
V_T	On-state voltage	$I_T = 15\text{ A}$	-	1.4	1.65			V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7	1.5			V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\ ^\circ\text{C}$	0.25	0.4	-			V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}; T_j = 125\ ^\circ\text{C}$	-	0.1	0.5			mA

DYNAMIC CHARACTERISTICS
 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	BT138- $V_{DM} = 67\% V_{DRM(max)}; T_j = 125\ ^\circ\text{C};$ exponential waveform; gate open circuit	...	...	...	250	-	V/ μs
dV_{com}/dt	Critical rate of change of commutating voltage	$V_{DM} = 400\text{ V}; T_j = 95\ ^\circ\text{C}; I_{T(RMS)} = 12\text{ A}; dl_{com}/dt = 5.4\text{ A/ms};$ gate open circuit	-	-	10	20	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 16\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A}; dl_G/dt = 5\text{ A}/\mu\text{s}$	-	-	-	2	-	μs





MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

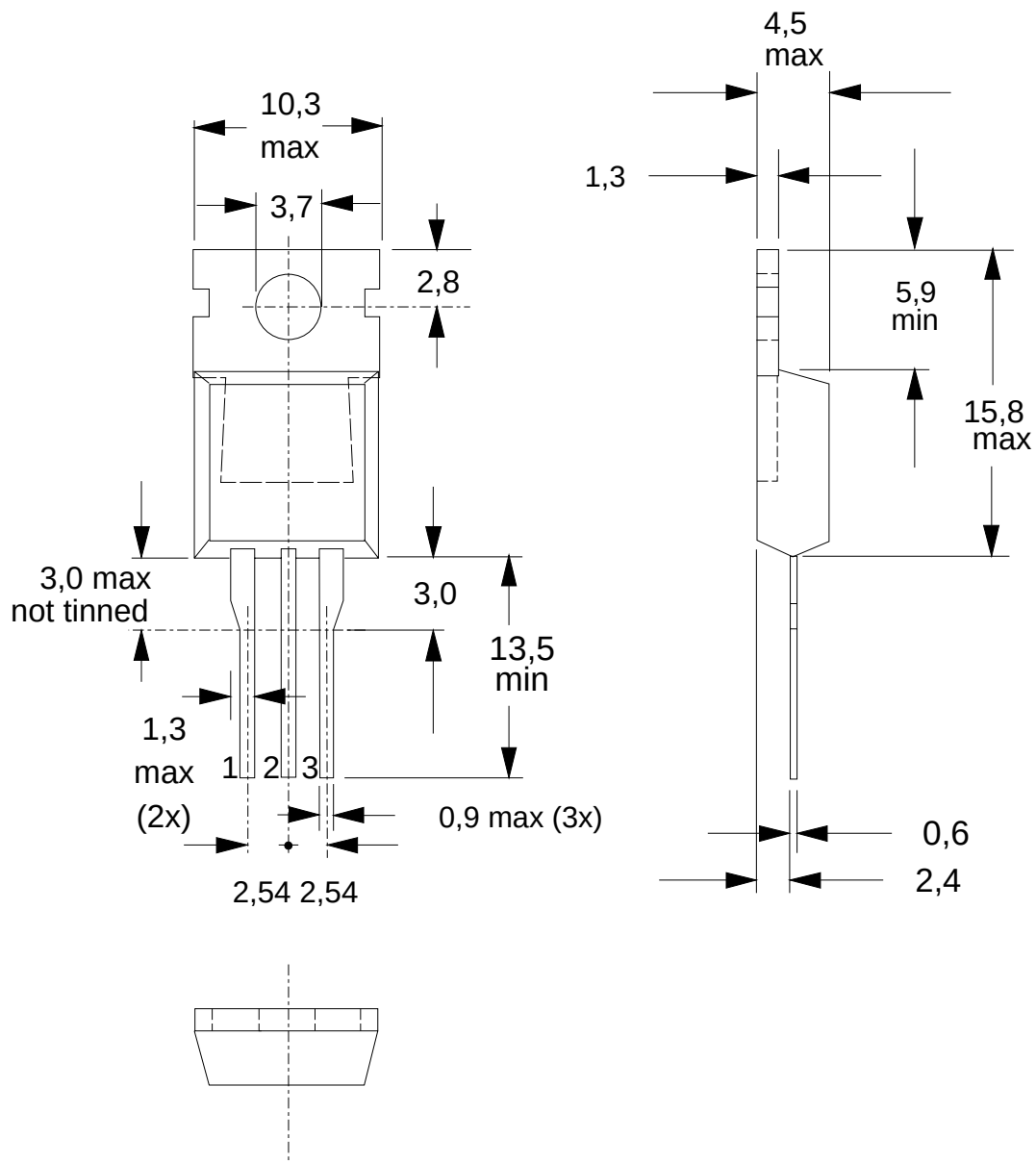


Fig.13. TO220AB; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".